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Quantum corrections to the conductivity of fermion–gauge field models: Application to half filled Landau level and high-T_c superconductors.

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Abstract

We calculate the Altshuler-Aronov type quantum correction to the conductivity of $2d$ charge carriers in a random potential (or random magnetic field) coupled to a transverse gauge field. The gauge fields considered simulate the effect of the Coulomb interaction for the fractional quantum Hall state at half filling and for the $t-J$ model of high-T_c superconducting compounds. We find an unusually large quantum correction varying linearly or quadratically with the logarithm of temperature, in different temperature regimes.

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I. INTRODUCTION.

Recent experiments on the fractional quantum Hall state at half-filling ($\nu = 1/2$) [1] and on the high temperature superconductor (HTSC) $La_{2-x}Sr_xCuO_2$ in a high magnetic field quenching the superconducting state [2] have revealed an unexpected logarithmic temperature dependence of the (longitudinal) resistivity ρ_{xx}. Similar behavior in HTSC compounds with low transition temperatures has been reported earlier in low or vanishing magnetic field [3–5]. There are several known sources of a logarithmical rise of resistivity with decreasing temperature. The first one, due to the Kondo effect [6] of localized magnetic spins, may be excluded here since the large magnetic fields employed in the FQHE [1] and in the HTSC [2] experiments would quench the Kondo effect up to a rather high energy scale. This eliminates the possibility of a $\ln T$ dependence at the observed low temperatures. Also, there is no indication of the existence of local moments in these systems. The second possible source is weak localisation (WL) of charge carriers in a $2d$ disordered potential. However, the large magnetic fields used in the experiments [1,2] destroy the quantum coherent backscattering effect responsible for WL. WL may contribute to the $\ln T$ behavior observed in HTSC in zero magnetic field [3–5], though. However, the magnitude of the $\ln T$ term found in these experiments is too large to be explained solely by the WL. The third effect giving rise to $\Delta\rho \sim \ln(1/T)$ at low temperature T derives from the quantum interference of impurity scattering and interaction between the charge carriers. Roughly speaking, the diffusive rather than ballistic motion of charge carriers in a random potential increases the time two interacting particles spend near each other and enhances therefore the interaction strength. In $2d$ the correction even diverges, eventually leading to the localization of the particles at zero temperature. The effect was discovered by Altshuler and Aronov (AA) [7], who obtained the quantum correction to the conductivity $\Delta\sigma = (e^2/h)\lambda_{AA}\ln(T\tau)$. Here e^2/h is the quantum unit of conductance, τ is the lifetime due to elastic scattering, and $\lambda_{AA} = \pi^{-1}(1 - \frac{3}{2}F)$ is a numerical coefficient. The quantity F is due to Hartree processes and is equal to the exact static scattering amplitude of a particle and a hole with total spin $j = 1$. It is usually positive, leading to partial cancellation of the exchange contribution represented by the first term (unity) in brackets,and tends to zero in the limit of weak screening. As we will discuss in detail below, the magnitude of the logarithmic term observed experimentally in HTSC materials and at $\nu = 1/2$ is typically a factor of $3 - 5$ larger than the AA result. As we will show, enhancement factors of this order may be obtained if the interaction by a fictitious gauge field is considered in addition to the usual Coulomb interaction.

The problem of particles interacting with a transverse gauge field was studied by Reizer [8] in the context of magnetic interaction of electrons in metals. More recently, its 2d version has attracted considerable interest [9] in connection with the gauge theory of high-T_c superconductors [10] and the Chern-Simons theory of the half-filled Landau level [11,12]. Both of these theories have definite successes in explaining the experimental situation and seem to capture at least the essential physics of the phenomena. This has motivated us to study in detail the low-temperature correction to conductivity in the framework of the above gauge theories. In the context of half-filled Landau level such a calculation was very recently done by Khveshchenko [13]. We find however that his results are incomplete (some of the temperature regimes are missing, some relevant parameters are not introduced) and contain some errors in the coefficients, which are crucial for comparison to the experimental

data.

II. QUANTUM CORRECTION TO CONDUCTIVITY OF FERMIONS COUPLED TO A TRANSVERSE GAUGE FIELD

We start from considering a simplified model of spinless fermions subject to a static random potential/magnetic field and coupled to a transverse gauge field, in the absense of any other interactions. Complications which arise in the cases of composite fermions at $\nu = 1/2$ and the gauge theory of high-T_c compounds will be discussed in the next two sections. The transverse part of the gauge field propagator is determined by the polarization tensor of fermions and has the form [8,9]

$$D_{\mu\nu}(\boldsymbol{q},\omega) = \frac{\delta_{\mu\nu} - \hat{q}_\mu \hat{q}_\nu}{i\omega\sigma(q,\omega) + \chi q^2} \ , \tag{1}$$

where $\hat{\boldsymbol{q}} = \boldsymbol{q}/|\boldsymbol{q}|$, and $\chi = 1/(24\pi m)$ is the diamagnetic susceptibility, with m being the fermion mass. The conductivity $\sigma(q,\omega)$ may be approximated by its static, long wavelength limit, $\sigma_0 = k_F l/4\pi$, with $k_F = (4\pi n)^{1/2}$ the Fermi wave number and l the transport mean free path.

The quantum correction to the conductivity is calculated following Altshuler and Aronov in lowest order of perturbation theory in the gauge field interaction for charge carriers diffusing in a random potential and/or random magnetic field. Vertex corrections due to impurity scattering are responsible for the singular enhancement of the interaction and are included consistently in lowest order in the disorder parameter $1/(E_F\tau_{tr})$, where E_F is the Fermi energy and τ_{tr} is the momentum (transport) relaxation time due to impurity scattering.

The two leading diagrams for the conductivity are shown in Fig.1. Three more diagrams included by AA are not relevant in the case of a transverse gauge field considered here, since they are not affected by diffusion poles. The solid lines in Fig.1 denote Green's functions

$$G(\boldsymbol{k},\epsilon_n) = [i\epsilon_n - \xi_k + (i/2\tau_k)sign(\epsilon_n)]^{-1} \ ,$$

where $\epsilon_n = (2n+1)\pi T$ is the Matsubara energy, $\xi_k = v_F(k - k_F)$ is the quasiparticle energy for momentum $\boldsymbol{k}$ and τ_k is the single particle relaxation time. As we shall show, the single particle time drops out of the final result, so we will not be concerned about the difficulties encountered with the definition of τ_k in the case of random magnetic fields [14,15]. The wavy line in Fig.1 represents the gauge field propagator, $D_{\mu\nu}(\boldsymbol{q},\omega)$, and the shaded blocks denote "diffusons" (particle-hole propagators), given by [16]

$$\Gamma_{kk'}(\boldsymbol{q},\omega_m) = (2\pi N_0)^{-1}\frac{\gamma_k\gamma^*_{k'}}{\omega_m + Dq^2} + \Gamma^{reg}_{kk'} \ , \tag{2}$$

assuming the energies of a particle and a hole have opposite signs. Here N_0 is the density of states at the Fermi level, D is the diffusion coefficient, and

$$\gamma_k = \frac{1}{\tau_k} - i\langle \boldsymbol{q}\boldsymbol{v}_{k_1}\tau_{k_1}\Gamma^{reg}_{kk_1}\rangle_{k_1} \ ,$$

where $\langle \ldots \rangle_k$ denotes averaging over the Fermi surface. At small frequency and momentum, $\Gamma_{kk'}$ is dominated by the singular contribution, which is given in the case of spatial isotropy, $\tau_k = \tau$, by

$$\Gamma_{kk'}(q, \omega_m) \simeq \frac{1}{2\pi N_0 \tau^2 (\omega_m + Dq^2)} \tag{3}$$

The regular part Γ^{reg} is however also important, since it determines the vertex renormalization, denoted by shaded triangles on Fig.1. Γ^{reg} may be expressed in terms of the eigenvalues λ_l and eigenfunctions Φ_k^l of the bare scattering cross section $w_{kk'}$ as

$$\Gamma^{reg}_{kk'} = \sum_{l \neq 0} \frac{\lambda_l}{1 - \lambda_l} \Phi_k^l \Phi_{k'}^{l*} \ ,$$

excluding the eigenvalue $\lambda_0 = 1$ associated with particle number conservation. The diffusion coefficient is defined in this framework as

$$D = \langle \tau_k v_{k\mu}^2 \rangle_k + \langle v_{k\mu} \tau_k \Gamma^{reg}_{kk'} \tau_{k'} v_{k'\mu} \rangle_{k,k'} \tag{4}$$

In the case of spatial isotropy $\Phi_k^l = (2\pi)^{-1/2} e^{il\phi_k}$ (ϕ_k is the polar angle of the momentum k), and eq.(4) reduces to

$$D = \frac{1}{2} v_F^2 \tau_{tr} \ ; \qquad \tau_{tr} = \frac{\tau}{1 - \lambda_1} \tag{5}$$

The velocity vertex $v_{k\mu}$ renormalizes to

$$J_{k\mu} = v_{k\mu} + \sum_{l \neq 0} \frac{\lambda_l}{1 - \lambda_l} \langle v_{k'\mu} \tau_{k'} \Phi_{k'}^l \rangle_{k'} \Phi_k^l = v_{k\mu} \frac{1}{1 - \lambda_1} = v_{k\mu} \frac{\tau_{tr}}{\tau} \tag{6}$$

This applies when the energy sign is opposite for two fermion lines attached to the vertex; otherwise, the vertex retains its bare form $v_{k\mu}$.

Now we calculate the conductivity correction represented by the two diagrams of Fig.1 (plus the same diagrams with reversed arrows) in the Matsubara technique. Each of the two fermion loops produces the factor $\pm 2\pi i N_0 \tau^2 \frac{v_F^2}{2}$. The diffuson is approximated by eq.(3) provided the two fermion lines it connects have opposite energy signs. This requirement implies that exactly two of four velocity vertices get renormalized according to eq.(6). Combining all this, we find that the total relaxation rate τ drops out, and the conductivity correction at a Matsubara frequency $\Omega_k > 0$ takes the following form:

$$\Delta\sigma(i\Omega_k, T) = -e^2 \frac{4}{\Omega_k} N_0 D^2 T \left\{ \sum_{\omega_l = 0}^{\Omega_k} \omega_l F(i\Omega_k, i\omega_l) + \sum_{\omega_l > \Omega_k} \Omega_k F(i\Omega_k, i\omega_l) \right\} \ , \tag{7}$$

where

$$F(i\Omega_k, i\omega_l) = \int \frac{d^2 q}{(2\pi)^2} \frac{1}{(Dq^2 + \Omega_k + \omega_l)(\omega_l \sigma(q) + \chi q^2)} \tag{8}$$

Carrying out the analytical continuation to real values of the frequency Ω, we get

$$\Delta\sigma(\Omega,T) = e^2\frac{N_0D^2}{i\pi\Omega}\int_{-\infty}^{\infty} d\omega\,\omega\coth\left(\frac{\omega}{2T}\right)\left[F(\Omega,\omega+\Omega)-F(\Omega,\omega)\right]\,, \tag{9}$$

with

$$F(\Omega,\omega) = \int\frac{d^2q}{(2\pi)^2}\frac{1}{(Dq^2-i\Omega-i\omega)(-i\omega\sigma(q)+\chi q^2)} \tag{10}$$

Now we are going to evaluate eqs.(9), (10) at zero external frequency Ω, when eq.(10) can be rewritten as

$$\begin{aligned}\Delta\sigma(T) &= -\frac{e^2N_0D^2}{i\pi}\int_{-\infty}^{\infty} d\omega F(0,\omega)\frac{\partial}{\partial\omega}\left[\omega\coth\frac{\omega}{2T}\right]\\ &\simeq -\mathrm{Im}\frac{2e^2N_0D^2}{\pi}\int_T^{1/\tau_{tr}} F(0,\omega)d\omega\end{aligned} \tag{11}$$

The integrand in eq.(10) has at $\Omega = 0$ three characteristic momentum scales, where its behavior changes:

i) $q_D = \sqrt{\omega/D} = l^{-1}\sqrt{2\omega\tau_{tr}}$, determined by the first factor in the denominator;

ii) $q_\chi = \sqrt{\omega\sigma_0/\chi} = k_F\sqrt{6\omega\tau_{tr}}$, determined by the second factor in the denominator;

iii) l^{-1}, which limits the applicability of the diffusion approximation.

Comparing these three scales, we see that q_D is the smallest one, whereas the relation between the other two depends on the value of frequency ω. We distinguish therefore the following two frequency domains:

i) $\omega \ll T_0 \equiv \dfrac{1}{6(k_Fl)^2\tau_{tr}}$.
In this region $q_\chi \ll l^{-1}$, and the integral (10) yields

$$\begin{aligned}F(0,\omega) &\simeq \frac{1}{2\pi}\int_0^\infty\frac{qdq}{(Dq^2-i\omega)(\chi q^2-i\omega\sigma_0)} \simeq \frac{i}{4\pi D\sigma_0\omega}\ln\frac{D\sigma_0}{\chi}\\ &= \frac{i}{2\pi N_0D^2\omega}\ln(\sqrt{3}k_Fl)\end{aligned} \tag{12}$$

ii) $\omega \gg T_0$.
In this case, $l^{-1} \ll q_\chi$, yielding

$$F(0,\omega) \simeq \frac{i}{2\pi N_0D^2\omega}\ln\frac{1}{lq_D} = \frac{i}{4\pi N_0D^2\omega}\ln\frac{1}{\omega\tau_{tr}} \tag{13}$$

Substituting eqs.(12), (13) in eq.(11), we get the following result for the correction to the conductivity

$$\Delta\sigma(T) = \frac{e^2}{2\pi h}\times\begin{cases}4\ln(\sqrt{3}k_Fl)\ln(T\tau_{tr})\,, & T\ll T_0\\ -\ln^2(T\tau_{tr})\,, & T_0\ll T\ll 1/\tau_{tr}\end{cases} \tag{14}$$

We see that at low temperatures the correction has the familiar $\ln T$ form, but with the coefficient enhanced by a large factor $2\ln(\sqrt{3}k_Fl)$ as compared to the usual Altshuler-Aronov result [7].

III. INTERACTION CORRECTION TO THE CONDUCTIVITY OF COMPOSITE FERMIONS AT HALF FILLING OF THE LANDAU LEVEL.

The longitudinal resistivity ρ_{xx} of a Hall bar in a strong magnetic field shows oscillations with minima at filling factors $\nu = p/(2p+1)$ of the lowest Landau level, where p is a positive or negative integer. For not too large values of p, $|p| = 1, 2, 3$, the resistivity is exactly zero at the minima and the Hall resistivity is quantized: $\rho_{xy} = \frac{2p+1}{p}\frac{h}{e^2}$. In the opposite limit $|p| \to \infty$, or $\nu \to 1/2$, ρ_{xx} tends to a finite limiting value, which is approached in a form of decaying oscillations, reminiscent of Shubnikov–de Haas oscillations in weak magnetic fields. This and other observations has been interpreted as indicating a kind of Fermi liquid state near $\nu = 1/2$. As a possible theoretical framework for this phenomenon, Jain [17] has proposed the composite fermion picture, in which a physical electron is replaced by a fermion threaded by a flux-tube carrying two flux quanta oriented oppositely to the external magnetic field B. The mean field generated by the flux tubes reduces the applied magnetic field to the effective field $B_{eff} = B - 4\pi cn/e$ (n is the electron density), which vanishes at half-filling. The quantized values of ν correspond to integer filling factors for the Landau levels in the effective fields, providing a natural explanation for the dominance of the observed plateau values.

A field-theoretical formalism implementing this idea with the help of a Chern-Simons (CS) gauge field has been worked out by Lopez and Fradkin [11]. Following a similar approach, Halperin, Lee and Read [12] have developed a theory for the half-filled Landau level, in which the fluctuations of the gauge field about the mean field are treated in the Random Phase Approximation (RPA). At this level of approximation, the transverse part of the gauge field propagator has the form (1). Here the renormalized diamagnetic susceptibility is given by [12,18]

$$\chi = \frac{1}{2\pi m^*}\left[\frac{1}{12} + \left(2\pi\sigma_{xy}^f + \frac{1}{2}\right)^2\right] + \frac{v(q)}{(4\pi)^2}\ , \tag{15}$$

where σ_{xy}^f is the Hall conductivity of composite fermions, which vanishes at $\nu = 1/2$, and $v(q)$ is the Coulomb interaction $v(q) = 2\pi e^2/\epsilon(q+\kappa)$, with ϵ being the dielectric constant. The screening parameter κ is governed by the polarization of external charges in gates, leads, doping layers, etc.

A. Unscreened Coulomb interaction.

In the case of unscreened Coulomb interaction, $v(q) = 2\pi e^2/\epsilon q$, the effective susceptibility χ is determined by the last term in eq.(15):

$$\chi \simeq \frac{e^2}{8\pi\epsilon q} \tag{16}$$

The momentum scale q_χ is now given by

$$q_\chi = \frac{2\epsilon k_F l}{e^2}\omega$$

Comparing it to q_D and l^{-1}, we find that one should distinguish now between the three following regions of frequency:

i) $\omega \ll T_1 \equiv \dfrac{C_*^2}{2(k_F l)^2 \tau_{tr}}$,
where $C_* = e^2 m^*/(\epsilon k_F)$ is a numerical constant, which is of order of 10 according to the experimental data [19]. In this low-frequency region we have $q_\chi \ll q_D \ll l^{-1}$, and the integral (10) can be estimated as

$$F(0,\omega) \simeq \frac{1}{2\pi}\frac{8\pi\epsilon}{e^2}\int_0^\infty \frac{dq}{Dq^2 - i\omega} = \frac{2\pi}{C_* v_F^2}\left(\frac{2i}{\omega\tau_{tr}}\right)^{1/2} \tag{17}$$

ii) $T_1 \ll \omega \ll T_2 \equiv \dfrac{C_*}{2k_F l \tau_{tr}}$.
In this domain $q_D \ll q_\chi \ll l^{-1}$, and we find

$$\begin{aligned} F(0,\omega) &\simeq \frac{1}{2\pi}\int \frac{qdq}{\left(-i\omega N_0 D + \frac{e^2}{8\pi\epsilon}q\right)(Dq^2 - i\omega)} \\ &\simeq \frac{i}{4\pi N_0 D^2 \omega}\ln\left[\frac{2}{C_*^2}(k_F l)^2 \omega\tau_{tr}\right] \end{aligned} \tag{18}$$

iii) $\omega \gg T_2$.
Now we have $q_D \ll l^{-1} \ll q_\chi$, and $F(0,\omega)$ is given by eq.(13).

Evaluating finally the frequency integral in eq.(11), we find the following correction to the conductivity

$$\Delta\sigma(T) = \frac{e^2}{2\pi h} \times \begin{cases} 2\pi\dfrac{k_F l}{C_*}\sqrt{T\tau_{tr}}\ , & T \ll T_1 \\ -\ln^2\left[\dfrac{2(k_F l)^2}{C_*^2}T\tau_{tr}\right]\ , & T_1 \ll T \ll T_2 \\ -\ln^2(T\tau_{tr})\ , & T_2 \ll T \ll 1/\tau_{tr} \end{cases} \tag{19}$$

B. Screened Coulomb interaction

Now we will suppose the Coulomb interaction to be screened with a short enough screening length $\kappa^{-1} \lesssim l$, so that its Fourier transform can be replaced by a constant

$$v(q) \simeq \frac{2\pi e^2}{\epsilon\kappa} = \frac{2\pi}{m^*}C_*\frac{k_F}{\kappa} \tag{20}$$

The susceptibility χ is then according to eq.(15) given by

$$\chi = \frac{1}{2\pi m^*}\left(\frac{1}{12} + \frac{1}{4} + \frac{1}{4}C_*\frac{k_F}{\kappa}\right) \tag{21}$$

Taking into account that $C_* \sim 10 \gg 1$ and $k_F/\kappa \gtrsim 1$, we can neglect all but the last term in eq.(21), so that

$$\chi \simeq \frac{C_*}{8\pi m^*}\frac{k_F}{\kappa} \tag{22}$$

The scale q_χ is now given by

$$q_\chi = \left(\frac{\omega\sigma_0}{\chi}\right)^{1/2} = \left(2\frac{\kappa}{k_F}\frac{k_F l}{C_*}m^*\omega\right)^{1/2} \tag{23}$$

We will assume that

$$\left(\frac{q_\chi}{q_D}\right)^2 = \frac{\kappa}{k_F C_*}(k_F l)^2 > 1 \ , \tag{24}$$

so that q_D is the smallest of the three scales q_D, q_χ and l^{-1}. As in section II, we find then two frequency domains:

i) $\omega \ll T_0^* \equiv \dfrac{C_*}{2}\dfrac{k_F}{\kappa}\dfrac{1}{(k_F l)^2\tau_{tr}}$.
In this case $q_D \ll q_\chi \ll l^{-1}$, and we get

$$\begin{aligned} F(0,\omega) &\simeq \frac{1}{2\pi}\int_0^\infty \frac{qdq}{(Dq^2 - i\omega)(\chi q^2 - i\sigma_0)} \simeq \frac{i}{4\pi N_0 D^2\omega}\ln\frac{N_0 D^2}{\chi} \\ &= \frac{i}{4\pi N_0 D^2\omega}\ln\left[\frac{(k_F l)^2}{C_*}\frac{\kappa}{k_F}\right] \end{aligned} \tag{25}$$

ii) $\omega \gg T_0^*$.
In this region $q_D \ll l^{-1} \ll q_\chi$, and $F(0,\omega)$ is given by eq.(13).

We find therefore the following correction to the conductivity

$$\Delta\sigma(T) = \frac{e^2}{2\pi h} \times \begin{cases} 4\ln\left[\left(\dfrac{\kappa}{C_* k_F}\right)^{1/2} k_F l\right]\ln(T\tau_{tr}) \ , & T \ll T_0^* \\ -\ln^2(T\tau_{tr}) \ , & T_0^* \ll T \ll 1/\tau_{tr} \end{cases} \tag{26}$$

Let us estimate the magnitude of the low-temperature logarithmic correction. We will take for this purpose the typical values of the parameters $k_F l = 2(h/e^2)\sigma_{xx}^f \simeq 50$ [1] and $C_* \simeq 10$ [19]. Further, we assume the screening length κ^{-1} to be of order of the spacer distance $d_s = 120nm$, so that $k_F/\kappa \sim 10$. Then the coefficient λ of the low-temperature correction

$$\Delta\sigma(T) = \frac{e^2}{h}\lambda\ln(T\tau_{tr}) \tag{27}$$

can be estimated as $\lambda \simeq \frac{2}{\pi}\ln 5 \simeq 1.0$. This value is in good agreement with the experimental results, $0.4 \leq \lambda \leq 1.6$ reported in Ref. [1]. We should note, however, that the transport mean free time τ_{tr} and the crossover temperature T_0^* are estimated with these values of

parameters as $1/\tau_{tr} \sim 0.5K$ and $T_0^* \sim 10 - 20mK$, so that the experimental data of Ref. [1] belong mainly to the high-temperature region (second line of eq.(26)). Though the slope $d\sigma/d\ln T$ of the corresponding log-squared behavior is the same at $T = T_0^*$ as for the simple logarithmic behavior at $T < T_0^*$, it is expected to decrease according to eq.(26) with T approaching $1/\tau_{tr}$. This would lead to a curvature of the graph $\sigma(\ln T)$; a feature, which seems not be observed in the experiment [1]. The reason of this discrepancy is not clear to us at the present stage.

IV. INTERACTION CORRECTION TO CONDUCTIVITY IN HTSC MATERIALS.

The properties of the high-T_c superconducting compounds are governed by the physics of the quasi-two-dimensional system of CuO_2-planes. A good candidate model is the $t-J$–Hamiltonian of two-dimensional electrons interacting via a nearest neighbor spin exchange interaction J and hopping on a square lattice with nearest neighbor amplitude t. Only the regime of small hole doping is of interest. The hopping is constrained to singly occupied lattice sites, on account of the large on site Coulomb repulsion on the Cu sites. It is difficult to implement the constraint in analytic approximations. A widely used method is the slave boson approach, in which bosons (b) are introduced to describe the empty lattice sites, in addition to two fermion (f) species with spin up and down. The constraint takes the form $b_i^\dagger b_i + \sum_\sigma f_{i\sigma}^\dagger f_{i\sigma} = 1$ for each lattice site i. A mean field approximation using the coherent hopping amplitudes $\langle b_i^\dagger b_i\rangle$, $\langle f_{i\sigma}^\dagger f_{i\sigma}\rangle$, the boson condensation amplitude $\langle b_i\rangle$, and the singlet pair amplitude $\langle f_{i\uparrow} f_{i\downarrow}\rangle$ as collective fields yields a phase diagram, which remarkably resembles experimental observations. We are here interested in the normal state properties at optimal doping, which is the phase where $\langle b_i^\dagger b_i\rangle$ and $\langle f_{i\sigma}^\dagger f_{i\sigma}\rangle$ are finite, while $\langle b_i\rangle$ and $\langle f_{i\uparrow} f_{i\downarrow}\rangle$ are zero (strange metal phase). In this phase the low energy fluctuations about the mean field may be described in terms of a $U(1)$ gauge field, introduced to restore the local constraint violated in mean field theory. The properties of the effective fermion–boson–gauge field theory have been discussed by Ioffe and Larkin and by Lee and Nagaosa among others [10]. The gauge field propagator has the form (1), with the conductivity σ and the susceptibility χ given now by the sum of fermion and boson contributions: $\sigma = \sigma_b + \sigma_f$, $\chi = \chi_b + \chi_f$. Since the concentration of bosons is equal to that of the holes and is therefore small for low doping, it is believed that $\sigma_b \ll \sigma_f$, so that the gauge field propagator (1) is determined essentially by the fermion polarization. For the fermion conductivity σ_f we could use therefore the above analysis of Sec.II with the final result (14). However, according to the Ioffe-Larkin composition rule, the physical conductivity (response to an external electromagnetic field) is given not by $\sigma = \sigma_b + \sigma_f$, but rather by $\sigma_{ph} = (\sigma_b^{-1} + \sigma_f^{-1})^{-1}$. Therefore, for $\sigma_b \ll \sigma_f$ we have $\sigma_{ph} \approx \sigma_b$, so that physical conductivity is dominated by bosons. One can argue that the repulsive interaction prevents them from Bose-condensation (except possibly at very low temperatures), and the bosons form a kind of Fermi surface. Then our above consideration in Sec.II can still be applied. However, since the diffusion coefficient D in eqs.(9), (10) refers now to bosons, whereas the conductivity σ entering the gauge field propagator corresponds to fermions, we get an extra small overall factor σ_b/σ_f in the final result, eq.(14). In addition, the factor $k_F l$ in the argument of the logarithm is replaced by $(k_B l k_F l_f)^{1/2}$, where k_B is a characteristic momentum of the bosons, and l_f and l are fermion and boson mean free paths,

respectively.

Let us compare these results with experimental findings. In ref. [3] data for the value of the coefficient λ of the logarithmic correction eq.(27) are presented for LaSrCuO samples with values of $k_F l$ ranging from 1 to 6. The corresponding λ's lie in the interval 0.8–1.8 and show a tendency of slight increase with the value of $k_F l$. These results are in a surprisingly good agreement with our eq.(14), but without the extra factor σ_b/σ_f. Similar conclusion can be drawn from the analysis of other experimental data [2,4,5].

We are thus forced to conclude that in the present state of the gauge theory of high-T_c materials, the magnitude of the correction to the physical conductivity due to the exchange of the gauge field is much smaller that its experimentally measured value, because of the small factor σ_b/σ_f. However, taking into account the rather good agreement between the experiment and the theoretical result (14) without this factor, it is tempting to speculate about possible modification of the gauge theory. The factor σ_b/σ_f would not appear, if $\sigma_f(q)$ would fall below $\sigma_b(q) \approx \sigma_b(0)$ for most of the q-regime of interest ($l_f^{-1} \ll q \ll l^{-1}$). This would require the characteristic momentum k_B in $\sigma_b \sim k_B l$ to be much larger than the Fermi momentum k_F. Alternatively, the effective gauge theory might include only one type of particles.

V. CONCLUSION.

We have calculated the quantum correction to the conductivity of charge carriers in a two-dimensional disordered system subject to a transverse gauge field interaction. We find the $\ln T$ behavior at low temperature, but with a coefficient strongly enhanced as compared to the usual Altshuler-Aronov result. At higher temperatures, a crossover to $\ln^2 T$ behavior is found. The results are in good quantitative agreement with the recently observed $\ln T$ dependence of the resistivity at half filling of the Landau level. We have also discussed the possible relevance of our results to the low temperature resistivity of high-T_c superconducting compounds in the framework of a gauge field model.

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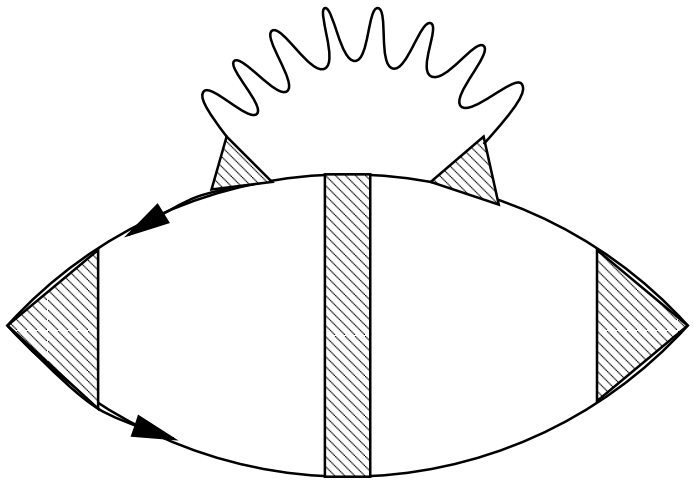
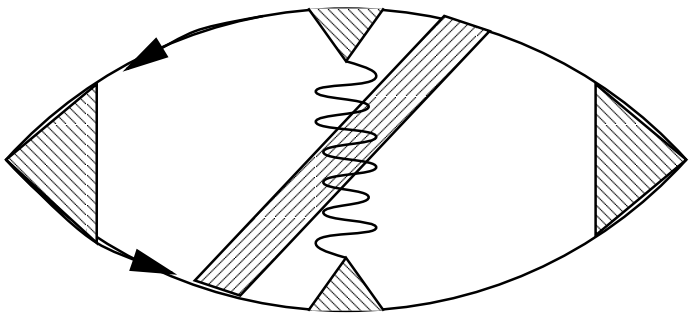
FIGURES

FIG. 1. Diagrams for the correction to conductivity due to a transverse gauge field interaction.



(a)



(b)